

G3S12010R

1200V/10A Silicon Carbide Power Schottky Barrier Diode

Features

- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behavior
- High temperature operation
- High frequency operation

Key Characteristics			
V _{RRM}	1200	V	
I _{F,} T _c ≤154°C	10	Α	
Qc	54.4	nC	

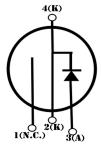
Benefits

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements

Applications

- SMPS, e.g., CCM PFC;
- Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV











Part No.	Package Type	Marking
G3S12010R	TO-252	G3S12010R

Maximum Ratings

Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		1200	
Surge Peak Reverse Voltage	V_{RSM}		1200	V
DC Blocking Voltage	V_{DC}		1200	
Continuous Forward Current	I _F	T_{C} =25 $^{\circ}$ C T_{C} =125 $^{\circ}$ C T_{C} =154 $^{\circ}$ C	32.4 17.4 10	Α
Repetitive Peak Forward Surge Current	I _{FRM}	T_c =25°C, tp=10ms, Half Sine Wave, D=0.3	50	Α
Non-repetitive Peak Forward Surge Current	I _{FSM}	T_{c} =25 $^{\circ}$ C, tp=10ms , Half Sine Wave	140	А
Power Dissipation	P _{TOT}	T _C =25℃	188	W
		T _C =110°C	81	W
Operating Junction	T _j		-55℃ to 175℃	$^{\circ}\!$
Storage Temperature	T_{stg}		-55℃ to 175℃	$^{\circ}\!$

Thermal Characteristic

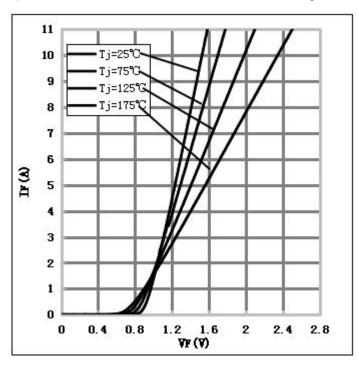
Parameter	Symbol T	Test Condition	Value	Unit
		rest Condition	Тур.	Unit
Thermal resistance from junction to case	R _{th JC}		0.84	°C/W

Electrical Characteristics

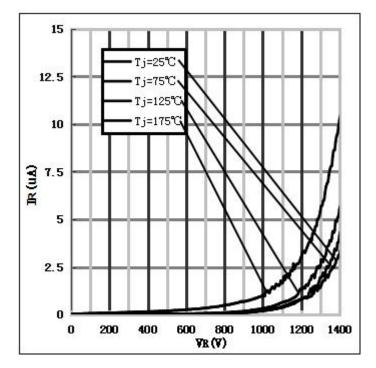
Parameter	Symbol	Test Conditions	Numerical		11
			Тур.	Max.	Unit
Forward Voltage	V _F	$I_F=10A, T_j=25$ °C	1.55	1.7	V
		$I_F=10A, T_j=175^{\circ}C$	2.35	2.6	V
Reverse Current	I _R	$V_R=1200V, T_j=25^{\circ}C$	0.7	50	μΑ
		$V_R=1200V, T_j=175$ °C	3	100	
Total Capacitive Charge	Q_{C}	$V_R=800V, T_j=150^{\circ}C$	54.4	-	nC
		$Qc = \int_0^{VR} C(V)dV$			
Total Capacitance	С	$V_R=0V$, $T_j=25$ °C, $f=1MHZ$	765	790	
		V_R =400V, T_j =25°C, f =1MHZ	50	54	pF
		$V_R=800V, T_j=25^{\circ}C, f=1MHZ$	48.5	51	

Performance Graphs

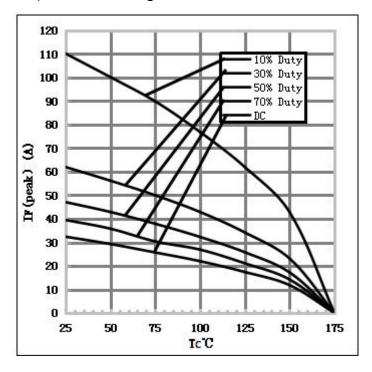
1) Forward IV characteristics as a function of Tj:



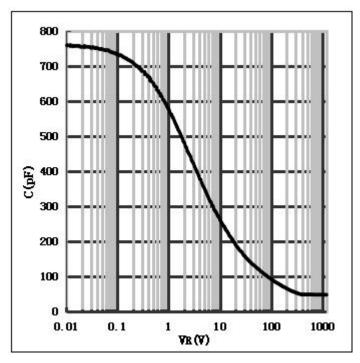
2) Reverse IV characteristics as a function of Tj:



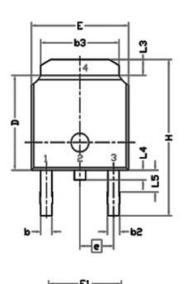
3) Current Derating:

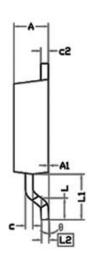


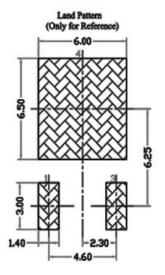
4) Capacitance vs. reverse voltage:

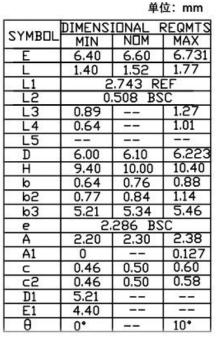


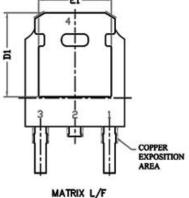
Package TO-252











Note:

- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- The Package Top May Be Smaller Than The Package Bottom.
- Dimension "b" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.10 mm Total In Excess Of "b" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.

Note: The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC(RoHS2). RoHS Certification and other certifications can be obtained from GPT sales representatives or GPT website: http://globalpowertech.cn/English/index.asp

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